



Adopt FRED chip
 Low forward Voltage drop
 Fast reverse recovery time
 High frequency operation
 High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
 Guard ring for enhanced ruggedness and long term reliability

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

: Tin plated leads, solderable per J-STD-002 and JESD22-B102

: As marked

(T_j=25 Unless otherwise specified

Device marking code			MURB1060CT
Repetitive Peak Reverse Voltage	V _{RRM}	V	600
Average Rectified Output Current @60Hz sine wave, R-load, T _c (FIG.1)	I _O	A	10
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _j =25	I _{FSM}	A	50
Current Squared Time @1ms t 8.3ms T _j =25	I ² t	A ² s	10
Storage Temperature	T _{stg}		-55 ~ +175
Junction Temperature	T _j		-55 ~ +175
Typical Junction capacitance @4V,1MHz	C _j	pF	20



Instantaneous forward voltage drop per diode	V_{FM}	V	$I_{FM}=5.0A @ T_j=25$	-	1.45	1.6	
			$I_{FM}=5.0A @ T_j=150$		1.15	1.3	
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	$V_{RM}=V_{RRM}$ $T_j=25$	-	-	5.0	
	I_{RRM2}		$V_{RM}=V_{RRM}$ $T_j=150$	-	35	200	
Reverse Recovery Time	T_{rr}	ns	$I_F=0.5A I_{RM}=1A$ $I_{RR}=0.25A T_j=25$	-	25	35	
			$T_j=25$	-	50.8	-	
			$T_j=125$	-	81.8	-	
Peak recovery current	I_{RRM}	A	$T_j=25$	$I_F=5A$ $di/dt=-200A/us$ $V_{RM}=200V$	-	3.06	-
			$T_j=125$		-	5.07	-
Reverse recovery charge	Q_{rr}	nC	$T_j=25$		-	78.88	-
			$T_j=125$		-	280	-

$T_j=25$ Unless otherwise specified

Thermal Resistance	Between junction and case	R J-C	/W	2.0
Thermal Resistance	Between junction and Air	R J-A	/W	50

(Example)

MURB1060CT	Approximate 1.43	800	/	8000	13° Reel
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